Unitized Semiconductor Devices - Page 1 of 1



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Inclosure Material:	
Plastic	
Overall Length:	
3.0 millimeters	
Overall Height:	
1.1 millimeters	
Overall Width:	
Between 1.5 millimete	ers and 1.7 millimeters
Function For Which	Designed:
Amplifier	
End Application:	
Ca70608-00 (19156)	, receiver-transmitter
Joint Electronic Dev	rice Engineering Council/jedec/case Outline Designation:
Mo-193, var.Aa, issi	ue c, dated january 2000
Component Name A	nd Quantity:
2 transistor	
Mounting Method:	
Press fit	
Semiconductor Mat	erial:
Silicon all transistor	
Voltage Rating In Vo	olts Per Characteristic:
60.0 collector to emit	ter voltage, dc all transistor and 60.0 collector to base voltage, dc all transistor and 5.0 emitter to base voltage, dc a
transistor	
Current Rating Per	Characteristic:
600.00 milliamperes	collector current, dc all transistor
Power Rating Per C	naracteristic:
700.0 milliwatts total	power dissipation all transistor
Maximum Operating	Tempurature Per Measurement Point:
150.0 degrees celsius	s junction
Product Name:	
Dwg- cage 19156: tr	ansistor array, general purpose amplifier; dwg- cage 7d893: pnp multi-chip general purpose amplifier
Special Features:	
Fairchild pkg: supers	ot-6
Terminal Type And	Quantity:
6 tab, solder lug	
Shelf Life:	
N/a	
Unit Of Measure:	
Demilitarization:	
No	
Fiig:	
A110a0	